



2018년 2월 7일(수), 09:00-10:30

Room C (함백, 5층)

D. Thin Film Process Technology 분과 [WC1-D] ALD/CVD Process (2D Materials)

WC1-D-1 09:00-09:15	Synthesis of 2-D SnS Thin Films and Their Potential Applications In-Hwan Baek ^{1,2} , Jung Joon Pyeon ^{1,3} , Taek-Mo Chung ⁴ , Jeong Hwan Han ⁵ , Cheol Seong Hwang ² , and Seong Keun Kim ¹ <i>¹Center for Electronic Materials, KIST, ²Department of Materials Science and Engineering, and Inter-University Semiconductor Research Center, Seoul National University, ³KU-KIST Graduate School of Converging Science and Technology, ⁴Division of Advanced M</i>
WC1-D-2 09:15-09:30	Characterizations of Charge-Trap Memory Thin-Film Transistors with HfO₂ Charge-Trap Layer Controlled by Atomic Layer Deposition Process So-Yeong Na and Sung-Min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i>
WC1-D-3 09:30-09:45	Synthesis of 2-Dimensional Single Phase SnS₂ by Atomic Layer Deposition Jung Joon Pyeon ^{1,2} , In-Hwan Baek ^{1,3} , Taek-Mo Chung ⁴ , Jeong Hwan Han ⁵ , Chong-Yun Kang ^{1,2} , Seong Keun Kim ¹ <i>¹Center for Electronic Materials, KIST, ²KU-KIST Graduate School of Converging Science and Technology, Korea University, ³Department of Materials Science and Engineering, and Inter-university Semiconductor Research Center, Seoul National University, ⁴Divi</i>
WC1-D-4 09:45-10:00	Continuous and Ultrathin ALD Ru Film Deposition Using Discrete Feeding Method (DFM) and Electric Field Assisted ALD (EA-ALD) Hyun Soo Jin and Tae Joo Park <i>Department of Materials Science and Chemical Engineering, Hanyang University</i>
WC1-D-5 10:00-10:15	Will Be Cubic BeO Thin Films the Next-Generation Dielectric? Seong Keun Kim ¹ , Woo Chul Lee ¹ , Eric S. Larsen ^{2,3} , Jung Hwan Yum ^{2,3} , and Christopher W. Bielawski ^{2,3} <i>¹Center for Electronic Materials, KIST, ²Department of Chemistry and Engineering, UNIST, ³Center for Multidimensional Carbon Materials (CMCM), Institute for Basic Science (IBS)</i>
WC1-D-6 10:15-10:30	High Growth Rate (> 0.25 nm/cycle) of Plasma-Enhanced Atomic-Layer-Deposited SiON Thin Film Using ICP Type Remote Plasma Dae Hyun Kim ¹ , Han Jin Lee ² , Hyun Soo Jin ² , Hyung Kun Lee ³ , Jeongsik Kim ³ , Min Ja Yoo ³ , Taewook Kim ³ , Jun Young Kim ³ , Mingun Lee ³ , Kyu Sung Cho ³ , Jae Woo Lee ³ , Jaehyun Kim ³ , and Tae Joo Park ^{1,2} <i>¹Department of Advanced Materials Engineering, Hanyang University, ²Department of Materials Science and Chemical Engineering, Hanyang University, ³Electronic Materials Business Division III, Dongjin Semichem</i>